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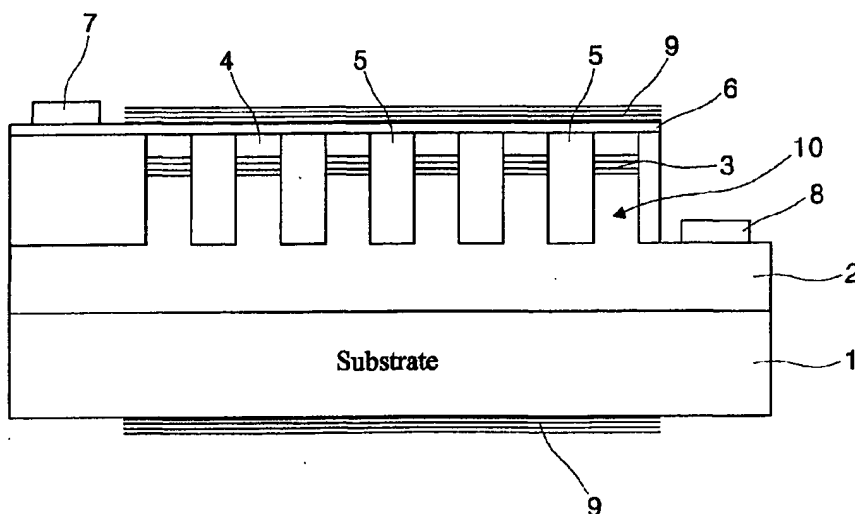
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ning of each regular issue of the PCT Gazette.

(54) Title: **NITRIDE MICRO LIGHT EMITTING DIODE WITH HIGH BRIGHTNESS AND METHOD OF MANUFACTURING THE SAME**



(57) Abstract: The present invention relates to a nitride micro light emitting diode (LED) with high brightness and a method of manufacturing the same. The present invention provides a nitride micro LED with high brightness and a method of manufacturing the same, wherein a plurality of micro-sized luminous pillars 10 are formed in a substrate, a gap filling material such as SiO₂, Si₃N₄, DBR(ZrO₂/SiO₂ HfO₂/SiO₂), polyamide or the like is filled in gaps between the micro-sized luminous pillars, a top surface 11 of the luminous pillar array and the gap filling material is planarized through a CMP processing, and then a transparent electrode 6 having a large area is formed thereon, so that all the luminous pillars can be driven at the same time. In addition, the present invention provides a nitride micro LED with high brightness in which uniformity in formation of electrodes on the micro-sized luminous pillars array is enhanced by employing a flip-chip structure.